J
SEMI
CONDUCTOR

#### **100V P-Channel Enhancement Mode MOSFET**

Current

Voltage

**Features** 

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@-10V,I<sub>D</sub>@-2.5A<650mΩ
- $R_{DS(ON)}$ ,  $V_{GS}$ @-4.5V, $I_D$ @-2A<700m $\Omega$

-100 V

- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

#### **Mechanical Data**

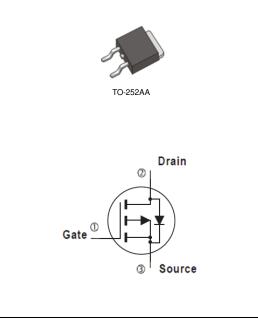
- Case: TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0104 ounces, 0.297grams

#### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMET	ER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-100	V
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V
	T <sub>C</sub> =25°C		-5	
Continuous Drain Current	T <sub>C</sub> =100°C	l <sub>D</sub>	-3.1	А
Pulsed Drain Current (Note 1)	T <sub>c</sub> =25°C	I <sub>DM</sub>	-10	
Power Dissipation	T <sub>C</sub> =25°C	5	30	
	T <sub>C</sub> =100°C	PD	12	W
Continuous Drain Current	T <sub>A</sub> =25°C		-1.3	А
	T <sub>A</sub> =70°C	I <sub>D</sub>	-1.1	А
Power Dissipation	T <sub>A</sub> =25°C		2.0	
Power Dissipation	T <sub>A</sub> =70°C	PD	1.3	W
Single Pulse Avalanche Energ	(Note 6)	E <sub>AS</sub>	1.3	mJ
Operating Junction and Storag		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance (Note 4,5)	Junction to Case	R <sub>θJC</sub>	4.2	°0.444
	Junction to Ambient	R <sub>θJA</sub>	62.5	°C/W

 P-2A<700mΩ ity

-5 A





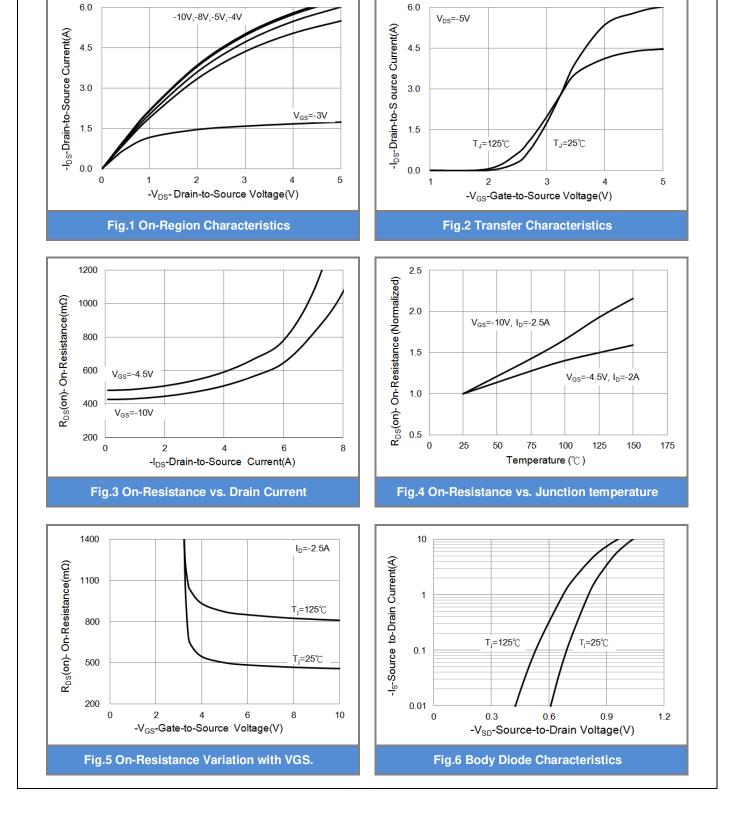


Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V,I_{D}=-250uA$	-100	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-1.0	-2.0	-2.5	V
		V <sub>GS</sub> =-10V,I <sub>D</sub> =-2.5A	-	500	650	mΩ
Drain-Source On-State Resistance	$R_{\text{DS(on)}}$	$V_{GS}$ =-4.5V,I <sub>D</sub> =-2A	-	560	700	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-80V, $V_{GS}$ =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 5)						
Total Gate Charge	Qg	$V_{DS}$ =-50V, I <sub>D</sub> =-5A, $V_{GS}$ =-10V <sup>(Note 1,2)</sup>	-	8	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	
Gate-Drain Charge	$Q_gd$		-	1.4	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	448	-	pF
Output Capacitance	Coss		-	28	-	
Reverse Transfer Capacitance	Crss		-	21	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DS}$ =-50V,RL=10 $\Omega$ , V <sub>GS</sub> =-10V, R <sub>G</sub> =6.2 $\Omega$ (Note 1,2)	-	3.7	-	ns
Turn-On Rise Time	tr		-	25	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	21	-	
Turn-Off Fall Time	t <sub>f</sub>		-	22	-	
Drain-Source Diode		•				
Maximum Continuous Drain-Source	I			-	-5	А
Diode Forward Current	I <sub>S</sub>		-			
Reverse Recovery Time	$V_{SD}$	I <sub>S</sub> =-1A,V <sub>GS</sub> =0V	-	-0.8	-1.2	V

NOTES :

- 1. Pulse width
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper
- 6. L=0.1mH, I<sub>AS</sub>=-5A, V<sub>GS</sub>=-10V, V<sub>DS</sub>=-25V, R<sub>G</sub>=25 ohm, Starting T<sub>J</sub>=25°C
- 7. Guaranteed by design, not subject to production testing.



**TYPICAL CHARACTERISTIC CURVES** 





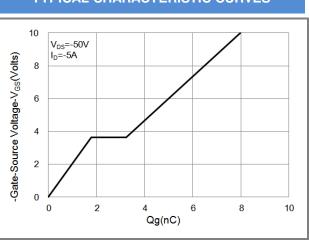


Fig.7 Gate-Charge Characteristics

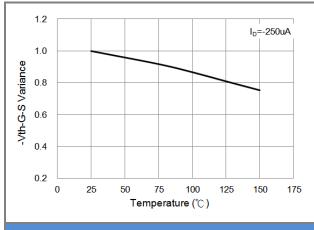
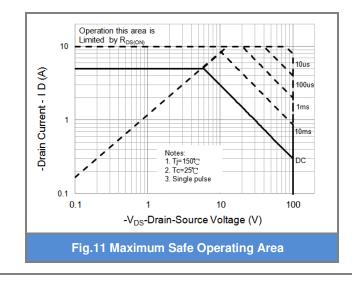
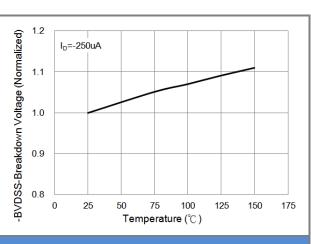


Fig.9 Threshold Voltage Variation with Temperature







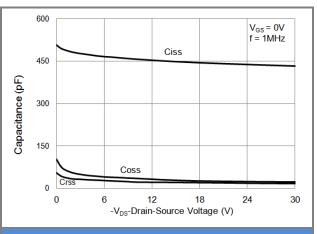
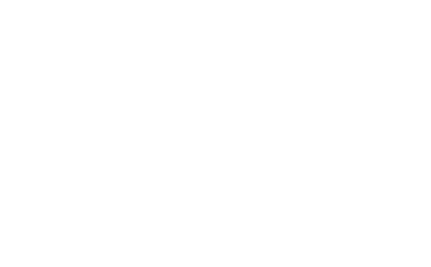


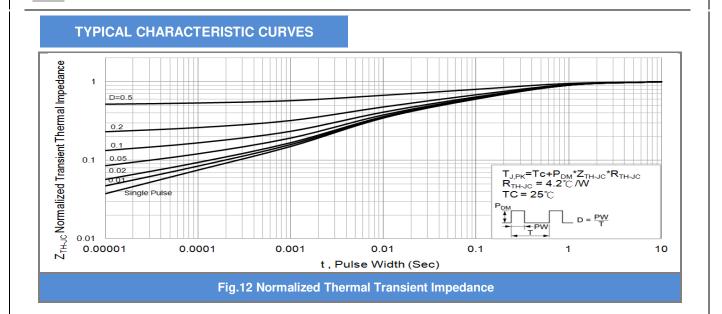
Fig.10 Capacitance vs. Drain-Source Voltage



PANJ





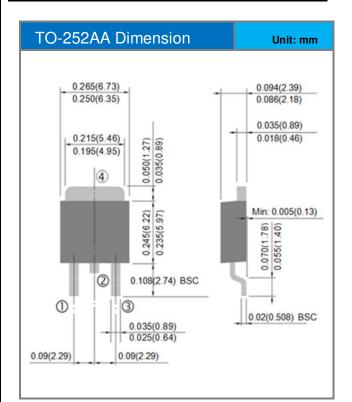


### 

PJD5P10A







#### **Packaging Information**



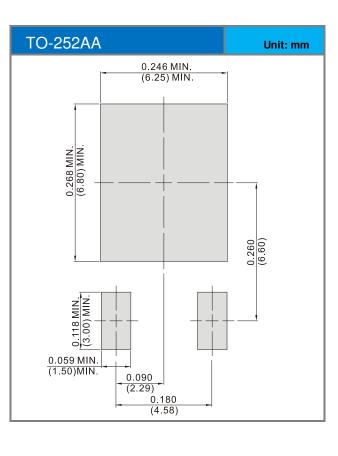




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD5P10A_L2_00001	TO-252AA	3,000pcs / 13" reel	D5P10A	Halogen free

#### MOUNTING PAD LAYOUT





### Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.